

N-Type 4H -SiC 6 inch Wafer



Property	Production Grade+	Production Grade	Research Grade	Dummy Grade
Diameter	150.0 mm ± 0.25 mm			
Surface Orientation	4.0° toward $\langle 11\bar{2}0 \rangle \pm 0.5^\circ$			
Primary Flat Orientation	$\{10\bar{1}0\} \pm 5.0^\circ$			
Secondary Flat Orientation	None			
Primary Flat Length	47.5 mm ± 2.0 mm			
Secondary Flat Length	None			
Micropipe Densities	≤ 1 cm ⁻²	≤ 5 cm ⁻²	≤ 10 cm ⁻²	≤ 50 cm ⁻²
Resistivity	0.015-0.028 Ω•cm			≤ 0.03 Ω•cm
Foreign Polytypes	0			≤ 15%
Thickness	350.0 μm ± 25.0 μm or 500.0 μm ± 25.0 μm			
TTV	≤ 15μm			≤ 20μm
Bow	≤ 40μm			≤ 60μm
Warp	≤ 60μm			
Surface Roughness	CMP Si Face Ra < 0.3 nm (10 μm × 10 μm)			CMP Si Face Ra < 0.5 nm (10 μm × 10 μm)
Edge Chips/Indents by Diffuse Lighting	None permitted		Qty.2 < 1.0mm width & depth	